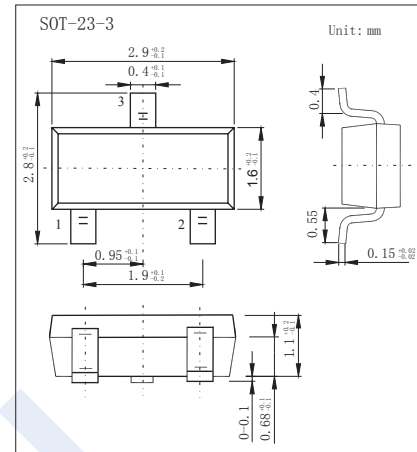


PIN Diodes

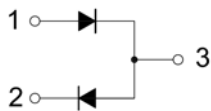
BAP64-04/05/06-HF (KAP64-04/05/06-HF)

■ Features

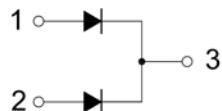
- High voltage, current controlled
- RF resistor for RF attenuators and switches
- Low diode capacitance
- Low diode forward resistance
- Low series inductance
- For applications up to 3 GHz.
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish



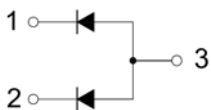
BAP64-04-HF



BAP64-05-HF



BAP64-06-HF

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Continuous Reverse Voltage	V_R	175	V
Continuous Forward Current	I_F	100	mA
Power Dissipation @ $T_s = 90^\circ\text{C}$	P_D	250	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	500	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-65 to 150	

PIN Diodes

BAP64-04/05/06-HF (KAP64-04/05/06-HF)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	V _F	I _F = 50 mA			1.1	V
Reverse voltage leakage current	I _R	V _R =175V			10	uA
		V _R =20 V			1	
Diode forward resistance (Note.1)	r _D	I _F = 0.5 mA , f = 100 MHz			40	Ω
		I _F = 1 mA , f = 100 MHz			20	
		I _F = 10 mA , f = 100 MHz			3.8	
		I _F = 100 mA , f = 100 MHz			1.35	
Diode capacitance	C _d	V _R = 0 V, f= 1 MHz		0.52		pF
		V _R = 1 V, f= 1 MHz			0.5	
		V _R = 20 V, f= 1 MHz			0.35	
Series inductance	L _s	I _F =10mA, f=100MHz		1.4		nH
Charge carrier life time	T _L	when switched from I _F = 10 mA to I _R = 6mA; R _L = 100 Ω; measured at I _R = 3 mA		1.55		us

Note.1: Guaranteed on AQL basis: inspection level S4, AQL 1.0.

■ Marking

NO	BAP64-04-HF	BAP64-05-HF	BAP64-06-HF
Marking	4K _F	5K _F	6K _F

PIN Diodes

BAP64-04/05/06-HF (KAP64-04/05/06-HF)

■ Typical Characteristics

